conductivity type, a third region of the first conductivity type, which is adjacent the second region and separated from the first region by the second region, and a fourth region of the first conductivity type which is separated from the second region by the third region and which has a higher doping concentration than the third region, the first, the second and the fourth region being provided with a terminal, characterized in that the third region is provided with a protection zone of the first conductivity type having a higher doping concentration than the third region, which protection zone is separated from the second region by the third region and is situated near the fourth region, and separated from said fourth region by an intermediate, comparatively high-impedance region, characterized in that the third region and the fourth region form, respectively, a drift region and a drain region of a Lateral DMOS transistor.

8. (Thrice Amended) A semiconductor device comprising a semiconductor body having a first region of a first conductivity type and, adjacent thereto, a second region of the second, opposite, conductivity type, wherein the first region electrically insulates the second region from a substrate of the second conductivity type, a third region of the first conductivity type, which is adjacent the second region and separated from the first

region by the second region, and a fourth region of the first conductivity type which is separated from the second region by the third region and which has a higher doping concentration than the third region, the first, the second and the fourth region being provided with a terminal, characterized in that the third region is provided with a protection zone of the first conductivity type having a higher doping concentration than the third region, which protection zone is separated from the second region by the third region and is situated near the fourth region, and separated from said fourth region by an intermediate, comparatively high-impedance region, characterized in that the device is of the RESURF type, wherein the product of the thickness and the doping concentration of the third region is approximately 10^{-2} atoms per cm^2.

Please add the following new Claim 9:

--9. (New) The semiconductor device of Claim 6, wherein the protection zone further comprises a ring around the fourth region.--

REMARKS

This application has been carefully reviewed in light of the Office Action dated May 22, 2002. Claims 6, 8, and 9 are now pending in this application. Claims 6 and 8 are the independent claims. Favorable reconsideration is respectfully requested.